ынона	0	0
出 エ T ロ F F I H I D F F I H I O		
COEEOGTO		
4	: 03	:05
Stamp	15	15
ស ក្ដ	21	21
Time	/80	08/
.u	2003/08/21	2003/08/21
	200	200
	<u></u>	
	USPAT; US-PGPUB; EPO; JPO	USPAT; US-PGPUB; EPO; JPO
DBs	- PG	- PG
ā	us JPO	J; US JPO
	F. F	, ti
	SPA PO;	USPA'
	nel\$1 and adj2 nescen\$4 or or capacitor EPO; s\$2) and and 1) or FET\$1 or	D H
	and nst card and and	
	en; ipac ar ar	
	id (channel\$1 an ight\$4 adj2 D or or luminescen\$4 \$7.ccls. or \$7.ccls. or fate and (capaci ppacitive\$2) and tric\$3) and tric\$3 and tric\$3 or	or or or or or
	ann ann ls. ls. ls. nd ive ive and	0000000
ex t	or o	2000 2000 2000 2000 2000 2000 2000 200
Ø E	anode and (charand (light\$4 or OLED or escen\$4 or lum d ((313/\$7.ccl) or 257/\$7.ccl) and (gate ance or capacitir dielectric\$3 t\$3 near2 islaror nor MOSFET\$1 or	5294870' (51629") 769292") 950950") 59861") 720432") 856429")
á	and (11i) OLED S4 O 13/\$; (9a) (9a) Cap	
Search	anode and (L or escen d ((3 or 2) and ce or r die t\$3 n	
ω	and and and ill of ld old old old or old it \$1	or or or or or or
•	and \$33 or E or	
	its its olu olu is) is) cc cc cc aci ats	4869 991" 4446" 761" 761" 826"
	odr S55 S55 S7 S7 S7 S7 S7 S7 S7 S7 S7 S7 S7 S7 S7	29 44 88 39 47 47
	cathode and anode and (impurits) and (((liberates)) or EL or OLED electroluminescens4 oluminous) and ((313/\$250/\$7.ccls.) and (gast) or capacitance or capor (insulats4 or dielect ((semiconducts3 near2 transistors1)))	(("5641991") c ("5641991") c ("5641991") c ("4885211") c ("5882761") c ("5839456") c ("4539507") c ("5643826") c ("5643826")).
m	cathode and anode and (channel\$1 & (impurit\$3) and ((light\$4 adj2 emit\$5) or EL or OLED or electroluminescen\$4 or luminescen\$1 luminous) and ((313/\$7.ccls. or 250/\$7.ccls. or 250/\$7.ccls. or 315/\$7.ccls. or 315/\$7.ccls.) and (gate and (capa or capacitance or capacitive\$2) and (insulat\$4 or dielectric\$3) and (semiconduct\$3 near2 island) or transistor\$1 or MOSFET\$1 or FET\$1 JFET\$1))))	
Hits ts	φ	_
	115	17
Туре	ω	&R
H	BRS	IS&R
	1	8

ш н н о н ю	<u> </u>	0
о н с н в н н в С н н в	0	<u> </u>
SOEE OH T W		
1	: 05	8 0
	ιΩ	
Stamp	T T	1 1
	2003/08/21	2003/08/21
Time	80/	/ 08
H	03	03
	700	200
	; US-PGPUB; JPO	US-PGPUB;
, ro	PGP	ъбъ
DBs	[S-]	[S-]
	T; Ui	JPO JPO
		PAT);
	USPA: EPO;	USPAT; EPO; JE
		or or
·	l H	(cathode 2 cen\$4) cls. or and tance or r t\$3 or
	or) or .)	rit\$3) and (cathornel\$1 and light\$4 adj2 ED or or luminescen\$4) or 250/\$7.ccls. c/\$7.ccls.) and r or capacitance insulat\$4 or (semiconduct\$3 ansistor\$1 or r JFET\$1)))))
	PRESENTATION	rit\$3) and (canel\$1 and light\$4 adj2 ED or or luminescen or 250/\$7.ccls/\$7.ccl
	0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0	and and Asin ls. ls. cr\$4 cr\$4 cr\$4
X t	Dacitance (("52948 541991") 73446") 885211") 882761") 339456") 539507") 643826")	urit\$3) and nnel\$1 and (light\$4 addibD or 250/\$7.c5/\$7.c5/\$7.c7/\$7
Text	acit ("5) (199 4199 7344 8521 8521 8276 3945 4382 4768	rits. nels: light light or or or 2: /\$7.0 r or insu insu ansis
ср	Capa 1d (("564 ("507 ("588 ("583 ("564 ("564	impurit\$3) and (channel\$1 and ((light\$4 adj2 r OLED or en\$4 or luminescls. or 250/\$7.cc 315/\$7.ccls.) a citor or capacit nd (insulat\$4 or nd ((semiconduct r transistor\$1)))
Search	and and ("") ("") ("") ("") ("") ("") ("") (""	(impurits3) (channel\$1 d ((light\$ or OLED or cen\$4 or lu cls. or 250 r 315/\$7.cc acitor or c and (insula and (semic or transist
യ്	U	channel\$1 and (impu and anode and (chandimpurit\$3) and (((emit\$5)) or EL or OLelectroluminescen\$4 and ((313/\$7.ccls.) 257/\$7.ccls. or 315 (gate and (capacitocapacitive\$2) and (dielectric\$3) and (near2 island) or tranoscen\$1 or FET\$1 or
	17 6	and and and and and references (calls. (calls. (calls. c\$2) and) or FI
	tor; 1 ive; 2 2 9 ") 9 2 2 9 ") 8 2 2 9 ") 6 2 9 ")	\$1 cc] und nd cc] rice
	25048 23948 23948 23948 23948	nnel\$ anode purit t\$5) ctrol (31. /\$7.co te ano aciti r2 is FET\$1
	(capacitor\$ capacitor\$ ("5294870") ("5151629") ("4769292") ("4950950") ("5059861") ("4356429") ("5923962")	channel\$1 and and and anode and (impurit\$3) and emit\$5) or EL electrolumines and ((313/\$7.ccls. o: 257/\$7.ccls. o: (gate and (cape capacitive\$2) dielectric\$3) enear2 island) emore island)
		010 - 0 0 0 00 0 2
t Ø		0 10 - 0 0 10 10 - 0 10 12
Hits		14
	0	
	0	414
Type Hits		14

ынонш	_	
м н н о н и и и и и и и и и и и и и и и и	0	0
	16	
⊲ Ω .	5:1	5:1
Stamp	_	ij
s t	/21	/21
Time	2003/08/21	2003/08/21
Ţ)3/)3/
	200	200
	o O	Q
	OPO	JPO
DBs	EPO;	EPO;
A		
·	USPAT;	d) or USPAT;
	SPZ	SPA
	Ч	D H
	and \$4) . or ce o	and \$4) . or ce o:
	3 12021	an 13.54.
	nd (channel\$1 and light\$4 adj2 ED or or luminescen\$4) or 250/\$7.ccls. c /\$7.ccls.) and r or capacitance insulat\$4 or (semiconduct\$3 ansistor\$1 or r JFET\$1)))))	nd (channel\$1 an light\$4 adj2 ED or or luminescen\$4 or 250/\$7.ccls.) and ror capacitance insulat\$4 or (semiconduct\$3 ansistor\$1 or r JFET\$1 or
	and (channel\$ (light\$4 adj2)LED or or 250/\$7.cc or 25/\$7.cc or capacit (insulat\$4 or (semiconduct (ransistor\$1)))	nd (channel\$ light\$4 adj2 ED or or luminesc or 250/\$7.cc /\$7.cc /\$7.ccls.) a r or capacit insulat\$4 or (semiconduct ansistor\$1 or r JFET\$1 or
	nd (channe light\$4 ad ED or or lumine or 250/\$7. /\$7.ccls.) r or capac insulat\$4 (semicondu ansistor\$1	node and (channe nd ((light\$4 ad or OLED or scen\$4 or lumine ccls. or 250/\$7. or 315/\$7.ccls.) pacitor or capac and (insulat\$4 and (semicondu or transistor\$1 or JFET\$1 o
Text	(C)	(C) Jht Or Or 255 7. C Sul Sul Sis FE
Ä	nd (challight\$4 Light\$4 ED or or lum: or 250/\$ /\$7.cclk r or calinsulat(semicoransisto) r JFET\$2	nd lig or or /\$7 /\$7 r o
rch	a) 10 4 5 1 5 1 5 1 5 1 5 1 5 1 5 1 5 1 5 1 5	and ((()ig OLED OLED of St. or St. or Cltor of C
Searc	lode a ((() or OL or OL or OL or 315 oacito and () or tr	ode (oor (oor 3 oor 3 oor 3 oor 3 oor 3 oor 4
ω	anode and (channe and ((light\$4 ad EL or OLED or nescen\$4 or lumine 7.ccls. or 250/\$7. or 315/\$7.ccls.) capacitor or capac 2) and (insulat\$4 3) and ((semicondud) or transistor\$1)	anode and (channel and (((light\$4 adj) EL or OLED or nescen\$4 or lumines 7.ccls. or 250/\$7.c. or 315/\$7.ccls.) capacitor or capacitos or capacitos or capacitos or capacitos or capacitos or capacitos or transistor\$1 or transistor\$1
	and \$3) or E umin 3/\$7 cls. d (c ve\$2 ic\$3 land	and (\$3) or E umin 3/\$7; cls. cls. icls. icls. icls. icls. or or
	ode uri \$5) trrc ((3) ((3) (3) (3) 2) 2) 2) 2) 2) 3) 3) 3) 3)	0de uri \$7.3 ((3 cit 2 i 2 i 1))
	cathode (impuri emit\$5) electro and ((3 257/\$7. (gate a capacit dielect near2 in MOSFET\$	cathode (impurit emit\$5) electrol and ((31 257/\$7.c (gate an capaciti dielectr near2 is MOSFET\$1
	cath (imp emit elec and 257/ (gat capa capa diel	catl (imm) emii elec and 257/ (gai (gai cape die nea MOSI
t 8		
Hits	178	178
Ø	Π	П
Туре	Ø	Ø
H	BRS	BRS
	ى	φ
		<u> </u>